# RT1P150X SERIES

**(Transistor)** 

UNIT: mm

Transistor With Resistor For Switching Application Silicon PNP Epitaxial Type

#### **DESCRIPTION**

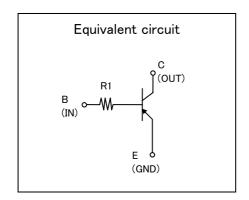
 $\label{eq:RT1P150X} \begin{array}{lll} \text{KRT1P150X} & \text{is} & \text{a} & \text{one chip transistor} \\ \text{with built-in bias resistor,NPN type is RT1N150X.} \end{array}$ 

### **FEATURE**

•Built-in bias resistor (R1=100k $\Omega$ ).

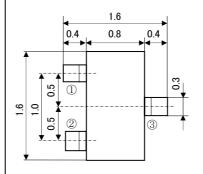
### **APPLICATION**

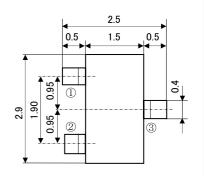
Inverted circuit, switching circuit, interface circuit, driver circuit.



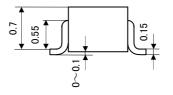
## OUTLINE DRAWING

RT1P150U





RT1P150C



JEITA: — JEDEC: —

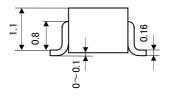
Terminal Connector

①:Base

2: Emitter

3: Collector

RT1P150M



JEITA: SC-59

JEDEC: Similar to TO-236

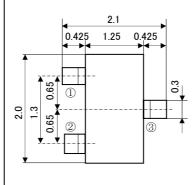
Terminal Connector

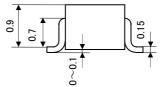
①:Base

2: Emitter

3: Collector

RT1P150S





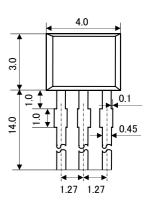
JEITA: SC-70 JEDEC: —

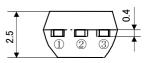
Terminal Connector

①:Base

2: Emitter

3: Collector





JEITA: — JEDEC: —

Terminal Connector

 $\bigcirc$ : Emitter

2: Collector

③:Base

# RT1P150X SERIES

**(Transistor)** 

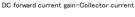
Transistor With Resistor For Switching Application Silicon PNP Epitaxial Type

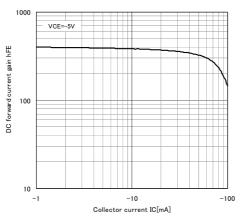
## MAXIMUM RATING (Ta=25°C)

SYMBOL	PARAMETER	RATING				LINIT
		RT1P150U	RT1P150M	RT1P150C	RT1P150S	UNIT
$V_{\text{CBO}}$	Collector to Base voltage	-50				
$V_{EBO}$	Emitter to Base voltage	-6				
$V_{CEO}$	Collector to Emitter voltage	-50				
Ιc	Collector current	-100				
I <sub>CM</sub>	Peak Collector current	-200				
Pc	Collector dissipation(Ta=25°C)	150	20	00	450	mW
Tj	Junction temperature	+150	+150 +150			°C
Tstg	Storage temperature	−55 <b>~</b> +150	−55 <b>~</b> +150			°C

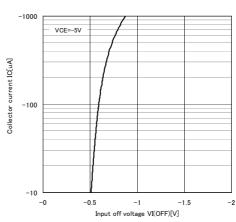
## ELECTRICAL CHARACTERISTICS (Ta=25°C)

SYMBOL	PARAMETER	TEST CONDITION	LIMIT			UNIT
		TEST CONDITION	MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$	C to E break down voltage	I <sub>C</sub> =-100 μ A, R <sub>BE</sub> =∞	-50			V
I <sub>CBO</sub>	Collector cut off current	$V_{CB}$ =-50V, I $_{E}$ =0			-0.1	μΑ
h <sub>FE</sub>	DC forward current gain	$V_{CE}$ =-5V, I <sub>C</sub> =-1mA	100			_
$V_{CE(sat)}$	C to E saturation voltage	I <sub>C</sub> =-1mA, I <sub>B</sub> =-0.1mA			-0.3	V
R <sub>1</sub>	Input resistance			100		kΩ
f <sub>⊤</sub>	Gain band width product	$V_{CE}$ =-6V, $I_{E}$ =10mA		150		MHz

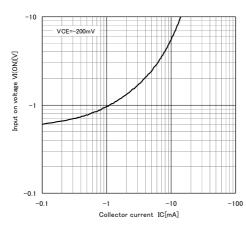




Collector current-Input off voltage



Input on voltage-Collector current





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